PCN	<b>PCN Number:</b> 20221219			9007.2			PCN E	Date:	December 21, 2022	
I ITIA ·				Fab site (RFAB) using qualified Process Technology, Die Revision,						
and additional Asse				e mbl	mbly & Test Sites & BOM options for select devices					
Cus	tomer	Contact:		<u>PCN</u>	<u>l Manager</u>		Dept:		Quality Services	
Proposed 1 <sup>st</sup> Ship Date:			I IIIn IX JII JA		e requests ted until:		Jan 20, 2023*			
*Sa	mple r	equests	received	a fte	fter Jan 20, 2023 will not be supported.					
Cha	Change Type:									
$\boxtimes$	Assem	bly Site		Assembly Process			Asser	mbly Materials		
$\boxtimes$	Desigr	1					Mech	anical Specification		
$\boxtimes$	Test S	ite		Packing/Shipping/Labeling			Test	Test Process		
	Wafer	Bump Sit	e	☐ Wafer Bump Material			Wafe	r Bump Process		
			$\boxtimes$	₩ Wafer Fab Materials						
				☐ Part number change						
		·			PCN Deta	ils				

### **Description of Change:**

Texas Instruments is pleased to announce the qualification of a new fab & process technology (RFAB, LBC9) and Assembly & Test sites & BOM option for selected devices as listed below in the product affected section. Construction differences are noted below:

С	urrent Fab Site	•	Additional Fab Site			
Current Fab Site			Additional Fab Site	Process	Wafer Diameter	
FR-BIP-1	ASLNONC10	200 mm	RFAB	LBC9	300 mm	

The die was also changed as a result of the process change.

Construction differences are as follows:

### **Group 1 devices:**

	HNA	HFTF
Mount Compound	SID#400180	SID#A-18
Bond wire composition, diameter	Au, 1.0 mil	Cu, 1.0 mil
Mold Compound	SID#450179	SID#R-27

### **Group 2 Device:**

	Current	Additional
Mount Compound	4042500	4147858
Bond wire composition, diameter	Au, 0.96 mil	Cu, 1.0 mil
Mold Compound	4206193	4211471

Test site changes as follows for Group 1 devices:

<b>Current Probe site</b>	Addn Probe site	Current final test site	Addn final test site	
FFAB	CDAT	HNA	HFTF	

For the group 2 device, the probe step will be removed, the final test site will remain the same.

Test coverage, insertions, conditions will remain consistent with current testing and verified with test MQ

The datasheets will be changing as a result of the above mentioned changes. The datasheet change details can be reviewed in the datasheet revision history shown below. The links to the revised datasheets are available in the table below.

Product Folder	Current Datasheet Number	New Datasheet Number	Link to full datasheet
SN74LVC1T45-Q1	SCES677D	SCES677E	https://www.ti.com/product/SN74LV C1T45-Q1
SN74LVC8T245-Q1	SCES815	SCES815A	https://www.ti.com/product/SN74LV C8T245-Q1



SN74LVC1T45-Q1

SCES677E - SEPTEMBER 2006 - REVISED DECEMBER 2022

### SN74LVC1T45-Q1 Automotive 1.65-V to 5.5-V Single-Bit Dual-Supply Level Shifter

### Changes from Revision D (July 2017) to Revision E (December 2022) Updated the numbering format for tables, figures, and cross-references throughout the document......1

- Updated the Switching Characterisitcs sections: extended some minimum specifications for lower delays......7



SN74LVC8T245-Q1

SCES815A - SEPTEMBER 2010 - REVISED DECEMBER 2022

## SN74LVC8T245-Q1-Q1 Automotive 8-Bit Dual-Supply Bus Transceiver With Configurable Voltage Translation and 3-State Outputs

### 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

### Changes from Revision \* (September 2010) to Revision A (December 2022)

- Added the Detailed Description sections, Application and Implementation sections, Power Supply
- Added thermal values

### Reason for Change:

Supply Continuity

### Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

### **Impact on Environmental Ratings**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
☑ No Change	☑ No Change	☑ No Change	⊠ No Change

### Changes to product identification resulting from this PCN:

### **Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
FR-BIP-1	TID	DEU	Freising
RFAB	RFB	USA	Richardson

### Die Rev:

Current	Ne W
Die Rev [2P]	Die Rev [2P]
-	A

HNA	HNT	THA CHN	Ayutthaya	
HFTFAT	HFT		<b>Hefei</b>	
Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City	

Sample product shipping label (not actual product label)



MADE IN: Malaysia 2DC: 2Q: MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

MSL 1 /235C/UNLI OPT: ITEM:

TTEM: 5A (L)TO:3750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483812 (P) (2P) REV: (V) 0033317

(2P) REV: (V) 0033317 (20L) CSO: CHE (2L) CCO-USA (22L) ASO: MLA (23L) ACO: MYS

### **Product Affected:**

**Group 1 devices:** 

SN74LVC1T45QDCKRQ1 SN74LVC1T45TDCKRQ1

**Group 2 device:** 

SN74LVC8T245QPWRQ1

# Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

### FAB5 LVC1T DCK-HFTF (Automotive) Approve Date 13-SEPTEMBER-2022

### Product Attributes

Attributes	Qual Device:	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:	
Atti ibutes	SN74LVC1T45QDCKRQ1	SN74LVC1T45TDCKRQ1	SN74HCS74QPWRQ1	SN74AUP1T34QDCKRQ1	SN74LVC1G17DCKR	
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1	-	
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125	-	
Product Function	Logic	Logic	-	Logic	-	
Wafer Fab Supplier	RFAB	RFAB	RFAB	MH8	FR-BIP-1	
Assembly Site	HFTFAT	HFTFAT	MLA	HFTFAT	TFME	
Package Group	SOT	SOT	TSSOP	SOT	SOT	
Package Designator	DCK	DCK	PW	DCK	DCK	
Pin Count	6	6	14	5	5	

- QBS: Qual By Similarity
   Qual Device SN74LVC1T45QDCKRQ1 is qualified at MSL1 260C
   Qual Device SN74LVC1T45TDCKRQ1 is qualified at MSL1 260C

### Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: SN74LVC1T45QDCKRQ1	Qual Device: SN74LVC1T45TDCKRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74AUP1T34QDCKRQ1
Test Group	A - Acc	elerated Enviror	nment Si	tress Tes	sts						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-		3/0/0	-
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	1/0/0	-	-	3/0/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-	-	3/231/0
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0	-	-	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	-	3/231/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	1/45/0	-	-	-
Test Group	B - Acc	elerated Lifetim	e Simula	tion Tes	ts						
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	1/77/0	-	3/231/0	1/77/0
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-

Test Group	C - Pack	age Assembly	Integrity	Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	1/30/0
SD	C3	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-	-	-	1/15/0	1/15/0
SD	C3	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	-	3/30/0	3/30/0
Test Group	D - Die F	abrication Relia	ability Te	sts							
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	rical Verificatio	n Tests								
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	-	1/3/0	-
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	1000 Volts		-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	-	1/3/0	-
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	-	1/6/0	-
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	-	3/90/0	3/90/0
Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	Qual Device	QBS Reference	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/Ik Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/Ik Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
   Grade 1 (or Q): -40C to +125C
   Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C
  - E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):
- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
   Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2109-074

Π Information Selective Disclosure

# Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

### FAB5 LVC1T DCK-HFTF (Automotive) Approve Date 13-SEPTEMBER-2022

### Qualification Results

									tai sample size / Totai i			
Туре		Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: SN74LVC1T45QDCKRQ1	Qual Device: SN74LVC1T45TDCKRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74AXC1T45QDCKRQ1	QBS Reference: SN74AUP1T34QDCKRQ1
Test Gr	oup A - A	ccelerated	Environ	ment Str	ess Tests							
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-	-	3/0/0	3/0/0	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	-	-	3/66/0	3/66/0	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	-	-	3/66/0	3/66/0	-
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	264 Hours	-	-	-	3/231/0	-
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	3/231/0	-	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	-
HAST	A2.1.3		3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	-	3/9/0	3/9/0	-
HAST	A2.1.4		3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	-	3/9/0	3/9/0	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	-	3/9/0	3/9/0	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	110C/85%RH	528 Hours	-	-	-	3/231/0	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	-	-	3/231/0	-	-
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	-	3/66/0	3/66/0	-
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	-	-	3/9/0	3/9/0	-
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	-	-	3/9/0	3/9/0	-
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	-	-	3/9/0	3/9/0	-
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	3/231/0	
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-	3/66/0	3/66/0	
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	-
тс	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	-	3/9/0	3/9/0	-
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	-	3/9/0	3/9/0	-
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires		-	3/9/0	3/9/0	
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	-	-	3/231/0	3/231/0	
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	-	3/66/0	3/66/0	
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	-
тс	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	-	-	3/9/0	3/9/0	-

тс	A4.2.4		3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	-	-	3/9/0	3/9/0	-
тс	A4.2.5		3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires		-	3/9/0	3/9/0	
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	-	3/135/0	3/135/0	
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	-
HTSL	A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	2000 Hours	-	-	3/135/0	3/135/0	-
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	-	3/3/0	3/3/0	-
Test Gr	roup B - A	Accelerated	Lifetim	e Simula	tion Tests							
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	1/77/0	-	3/231/0	3/231/0	1/77/0
ELFR	В2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	3/2400/0	-	
Test Gr	roup C - F	Package As	sembly	Integrity	/ Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0		3/90/0	3/90/0	1/30/0
WBP	C2	MIL- STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	-	3/90/0	3/90/0	1/30/0
SD	СЗ	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-		-	1/15/0	-	1/15/0
SD	СЗ	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	1/15/0	-	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67		1/10/0	-	3/30/0	3/30/0	3/30/0
Test Gr	roup D - [	Die Fabricat	ion Reli	ability Te	ests							
ЕМ	D1	JESD61	-		Electromigration	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-		Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Gro	oup E - El	lectrical Ve	rification	Tests								
	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0		1/3/0	1/3/0	
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	1000 Volts			-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0		1/3/0	1/3/0	-
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004		1/6/0		1/6/0	1/6/0	-
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold		3/90/0		3/90/0	3/90/0	3/90/0
										1		

- QBS: Qual By Similarity
   Qual Device SN74LVC1T45QDCKRQ1 is qualified at MSL1 260C
   Qual Device SN74LVC1T45TDCKRQ1 is qualified at MSL1 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
  The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47:-55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
   Grade 2 (or T): -40C to +105C
   Grade 3 (or I): -40C to +85C

### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
   Room: AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2109-074

# Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

# FAB5 LVC8T PW-MLA (Automotive) Approve Date 31-MARCH -2022

### Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:
Atti ibutes	SN74LVC8T245QPWRQ1	SN74HCS74QPWRQ1	SN74AXC8T245QPWRQ1	SN74LXC8T245QPWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125	-40 to 125
Product Function	Logic	Logic	Logic	Logic
Wafer Fab Supplier	RFAB	RFAB	MH8	RFAB
Assembly Site	MLA	MLA	MLA	MLA
Package Group	TSSOP	TSSOP	TSSOP	TSSOP
Package Designator	PW	PW	PW	PW
Pin Count	24	14	24	24

- QBS: Qual By Similarity
   Qual Device SN74LVC8T245QPWRQ1 is qualified at MSL1 260C

### Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: SN74LVC8T245QPWRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74AXC8T245QPWRQ1	QBS Reference: SN74LXC8T245QPWRQ1
Test Group	A - Acce	lerated Environ	ment St	ress Tes	its						
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-	3/0/0	3/0/0	-
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	1/0/0	-	3/0/0	1/0/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-	-	1/77/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	1/77/0	-	-	-
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	1/77/0	-	3/231/0	1/77/0
AC/UHAST	АЗ	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	130C/85%RH	96 Hours	1/77/0	-	3/231/0	1/77/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	-	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0	-
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles		-		1/77/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	-	-	-
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	-	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	3/135/0	-

HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	1/45/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	1/45/0	-	-	-
Test Group	B - Acce	elerated Lifetime	e Simula	tion Test	ts						
		JEDEC									
HTOL	B1	JESD22- A108	1	77	Life Test	125C	1000 Hours	1/77/0	3/231/0	3/231/0	1/77/0
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0		-
Test Group	C - Pack	age Assembly	Integrity	Tests							
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
SD	С3	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	1/15/0	-	-
SD	СЗ	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	1/15/0	-	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-	1/10/0
Test Group	D - Die F	abrication Relia	ability Te	sts							
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elect	trical Verification	n Tests								
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0		
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	4500 Volts	-	-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	2000 Volts	-	-	-	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0	-	-
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	1/6/0	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	3/90/0	3/90/0
Additional 1	Tests										
	T										
Туре	#	Test Spec	Min Lot	SSI	Test Name	Condition	Duration	Qual Device	QBS Reference	QBS Reference	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours

  The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, and 170C/420 Hours

  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 1 (or Q): -40C to +125C
   Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

### E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2110-039

TI Informatio Selective Disclosur

# Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

### FAB5 LVC8T PW-MLA (Automotive) Approve Date 31-MARCH -2022

### Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:	QBS Reference:
Ambutes	SN74LVC8T245QPWRQ1	SN74HCS74QPWRQ1	SN74AXC8T245QPWRQ1	SN74LXC8T245QPWRQ1
Die Attributes				
Wafer Fab Supplier	RFAB	RFAB	MH8	RFAB
Wafer Process	LBC9	LBC9	LBC7T	LBC9
Die Size (L,W) (um)	890 x 1130	460 x 510	882.8 x 1166.3	940 x 1180
Package Attributes				
Assembly Site	MLA	MLA	MLA	MLA
Package Group	TSSOP	TSSOP	TSSOP	TSSOP
Package Designator	PW	PW	PW	PW
Package Size (mm)	7.8 x 4.4	5 x 4.4	7.8 x 4.4	7.8 x 4.4
Body Thickness (mm)	1	1	1	1
Pin Count	24	14	24	24
·				

Bond Wire Composition	CU	CU	CU	CU
Bond Wire Diameter(um)	25.4	20.32	25.4	25.4

- QBS: Qual By Similarity
   Qual Device SN74LVC8T245QPWRQ1 is qualified at MSL1 260C

### Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: SN74LVC8T245QPWRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74AXC8T245QPWRQ1	QBS Reference: SN74LXC8T245QPWRQ1
Test G	roup A - /	Accelerated	Enviror	nment St	ress Tests						
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL1 260C	1 Step	-	3/0/0	3/0/0	-
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	-	3/66/0	3/66/0	-
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	-	3/66/0	3/66/0	-
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	-	3/231/0	3/217/0	-
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	-	3/66/0	3/66/0	-
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0	-
тс	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	3/66/0	3/66/0	-
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	3/9/0	3/9/0	-
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	-	3/231/0	3/210/0	-
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	-	3/66/0	3/66/0	-
тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
	_										

TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	-	3/9/0	3/9/0	-
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	3/135/0	-
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
HTSL	A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	2000 Hours	-	3/135/0	3/133/0	-
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	-	3/3/0	3/3/0	-
Test Gr	oup B - A	Accelerated	Lifetime	Simula	tion Tests						
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	1/77/0	3/231/0	3/231/0	1/77/0
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-	-
Test Gr	oup C - F	ackage As:	sembly I	ntegrity	Tests						
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
WBP	C2	MIL- STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	3/90/0	1/30/0
SD	C3	JEDEC JESD22- B102	1	15	PB Solderability	>95% Lead Coverage	-	1/15/0	1/15/0	-	-
SD	C3	JEDEC JESD22- B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	1/15/0	-	-
		JEDEC JESD22-			Physical						
PD	C4	B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-	1/10/0
		and			Dimensions	Cpk>1.67	-	1/10/0	3/30/0	-	1/10/0
		and B108			Dimensions	Cpk>1.67	-	1/10/0  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	1/10/0  Completed Per Process Technology Requirements
Test Gr	oup D - C	and B108 Die Fabricati		bility Te	Dimensions sts	Cpk>1.67	-	Completed Per Process Technology	Completed Per Process Technology		Completed Per Process
Test Gr	oup D - E	and B108 Die Fabricati	ion Relia	bility Te:	Dimensions sts  Electromigration Time Dependent Dielectric		-	Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements Completed Per Process Technology	Technology Requirements  Completed Per Process	Completed Per Process Technology Requirements Completed Per Process
Test Gr EM TDDB	D1	and B108 Die Fabricati  JESD61  JESD35  JESD60	ion Relia	bility Te	Electromigration Time Dependent Dielectric Breakdown Hot Carrier		-	Completed Per Process Technology Requirements Completed Per Process Technology Requirements Completed Per Process Technology	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology	Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process
Test Gr EM TDDB	D1 D2 D3	and B108 Die Fabricati  JESD61  JESD35  JESD60	ion Relia	bility Te	Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process Technology Requirements  Completed Per Process	Completed Per Process Technology Requirements
Test Gr EM TDDB HCI NBTI SM	D1 D2 D3 D4 D5	JESD61  JESD65  JESD660  & 28	ion Relia	bility Te	Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Gr EM TDDB HCI NBTI SM	D1 D2 D3 D4 D5	JESD61  JESD61  JESD60  JESD60  JESD60  JESD60	ion Relia	bility Te	Electromigration Time Dependent Dielectric Breakdown Hot Carrier Injection Negative Bias Temperature Instability		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Gr EM TDDB HCI NBTI SM Test G	D1 D2 D3 D4 D5 Group E -	JESD61  JESD61  JESD60 & 28  -  Electrical Ve	on Relia	bility Te	Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration		-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TEST GEM TDDB HCI NBTI SM Test G	D1  D2  D3  D4  D5  E2	JESD61  JESD61  JESD60 & 28  -  -  Electrical Ve Q100-002  AEC Q100-	rificatio	bility Te	Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration  ESD HBM		2000 Voits	Completed Per Process Technology Requirements  Technology Requirements  1/3/0	Completed Per Process Technology Requirements  Completed Per Process Technology Requirements	Technology Requirements  Completed Per Process Technology Requirements  -	Completed Per Process Technology Requirements  -
Test Gr EM TDDB HCI NBTI SM Test G ESD	D1 D2 D3 D4 D5 FOUP E-	JESD61  JESD61  JESD60  JESD60  & 28  -  -  Electrical Vel AEC Q100- 002  AEC Q100- Q100- Q100- Q100-	1		Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration  ESD HBM  ESD HBM	-	- 2000 Volts	Completed Per Process Technology Requirements  1/3/0	Completed Per Process Technology Requirements  1/3/0	Technology Requirements  Completed Per Process Technology Requirements  -	Completed Per Process Technology Requirements  - 1/3/0
Test Cr EM TDDB HCI NBTI SM Test Cr ESD	D1  D2  D3  D4  D5  roupE-  E2  E3	JESD61  JESD61  JESD60  JESD60  AEC Q100-002  AEC Q100-011  AEC Q100-011  AEC Q100-011  AEC Q100-011	1 1 1	n Tests 3 3 3	Dimensions  Electromigration  Time Dependent Dielectric Breakdown  Hot Carrier Injection  Negative Bias Temperature Instability  Stress Migration  ESD HBM  ESD HBM  ESD CDM	-	- 2000 Volts 4500 Volts 2000 Volts	Completed Per Process Technology Requirements  1/3/0  -	Completed Per Process Technology Requirements  1/3/0  -	Technology Requirements  Completed Per Process Technology Requirements	Completed Per Process Technology Requirements  - 1/3/0  1/3/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/Ik Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
  The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/Ik Hours, and 170C/420 Hours
  The following are equivalent Temp Cycle options per JESD47:-55C/125C/700 Cycles and -65C/150C/500 Cycles

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +1250
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level)

- Room/Hot/Cold : HTOL, ED
- . Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2110-039

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